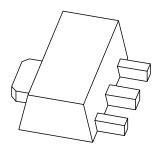
## **DISCRETE SEMICONDUCTORS**

## DATA SHEET



# **BF621; BF623**PNP high-voltage transistors

Product data sheet Supersedes data of 1999 Apr 21 2004 Dec 14



## **PNP** high-voltage transistors

BF621; BF623

#### **FEATURES**

- Low current (max. 50 mA)
- High voltage (max. 300 V).

#### **APPLICATIONS**

· Video output stages.

#### **DESCRIPTION**

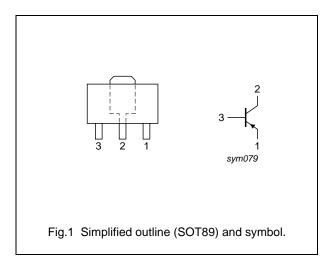
PNP high-voltage transistor in a SOT89 plastic package. NPN complements: BF620 and BF622.

#### **MARKING**

TYPE NUMBER	MARKING CODE
BF621	DF
BF623	DB

#### **PINNING**

PIN	DESCRIPTION
1	emitter
2	collector
3	base



#### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE		
ITPE NUMBER	NAME DESCRIPTION		VERSION	
BF621	SC-62	plastic surface mounted package; collector pad for good heat	SOT89	
BF623		transfer; 3 leads		

## PNP high-voltage transistors

BF621; BF623

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

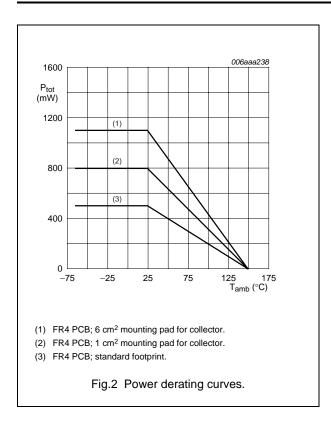
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BF621		_	-300	V
	BF623		_	-250	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BF621		_	-300	V
	BF623		_	-250	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	<b>-</b> 5	V
I <sub>C</sub>	collector current (DC)		_	-50	mA
I <sub>CM</sub>	peak collector current		_	-100	mA
I <sub>BM</sub>	peak base current		_	-50	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
		note 1	_	0.5	W
		note 2	_	0.8	W
		note 3	_	1.1	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

#### Notes

- 1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
- 2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.
- 3. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

## PNP high-voltage transistors

BF621; BF623



2004 Dec 14

## PNP high-voltage transistors

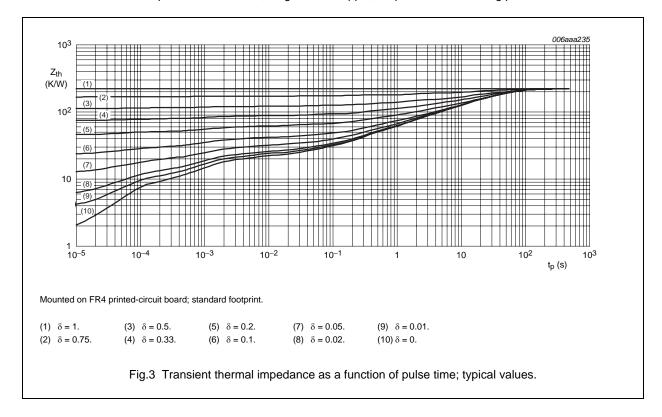
BF621; BF623

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to	in free air		
	ambient	note 1	250	K/W
		note 2	156	K/W
		note 3	113	K/W
R <sub>th(j-s)</sub>	thermal resistance from junction to soldering point		30	K/W

#### **Notes**

- 1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
- 2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.



## PNP high-voltage transistors

(4)  $\delta = 0.33$ .

(6)  $\delta = 0.1$ .

BF621; BF623

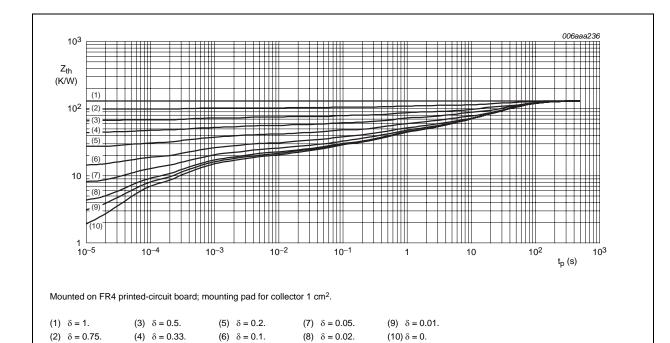
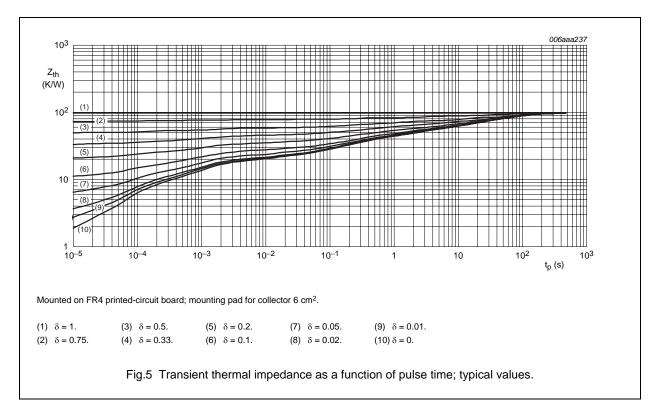


Fig.4 Transient thermal impedance as a function of pulse time; typical values.

(8)  $\delta = 0.02$ .



2004 Dec 14 6

(2)  $\delta = 0.75$ .

## PNP high-voltage transistors

BF621; BF623

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	I <sub>E</sub> = 0 A; V <sub>CB</sub> = -200 V	_	-10	nA
		$I_E = 0 \text{ A}; V_{CB} = -200 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-10	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$I_C = 0 \text{ A}; V_{EB} = -5 \text{ V}$	_	-50	nA
h <sub>FE</sub>	DC current gain	$I_C = -25 \text{ mA}; V_{CE} = -20 \text{ V}$	50	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -30 \text{ mA}; I_B = -5 \text{ mA}$	_	-800	mV
C <sub>re</sub>	feedback capacitance	$I_C = i_c = 0 \text{ A}; V_{CE} = -30 \text{ V}; f = 1 \text{ MHz}$	_	1.6	pF
f <sub>T</sub>	transition frequency	$I_C = -10 \text{ mA}$ ; $V_{CE} = -10 \text{ V}$ ; $f = 100 \text{ MHz}$	60	_	MHz

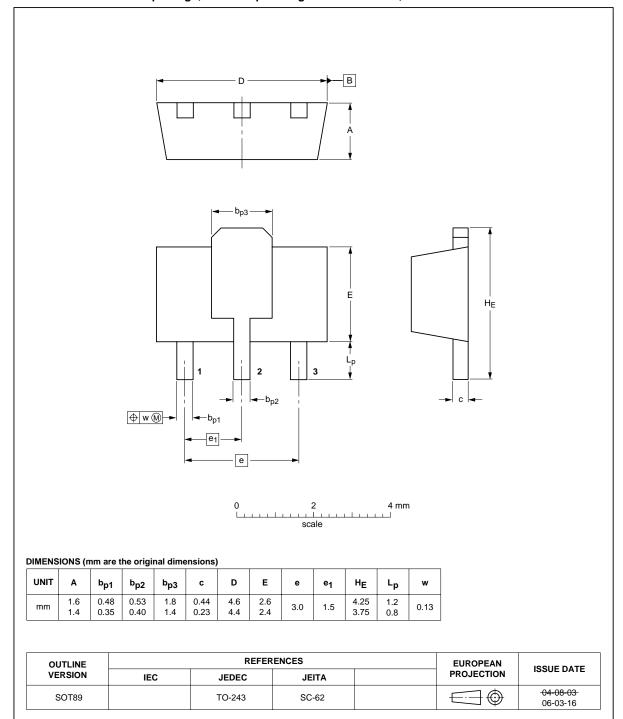
## PNP high-voltage transistors

BF621; BF623

#### **PACKAGE OUTLINE**

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

**SOT89** 



## PNP high-voltage transistors

BF621; BF623

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

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Printed in The Netherlands R75/04/pp10 Date of release: 2004 Dec 14 Document order number: 9397 750 13868

